





EH29 25 ET

RoHS Compliant (Pb-free) 1.8V 4 Pad 5mm x 7mm Ceramic SMD LVCMOS Oscillator

Series -

Frequency Tolerance/Stability ±25ppm Maximum

Operating Temperature Range --40°C to +85°C

TS -5.000M

- Nominal Frequency 5.000MHz

L Pin 1 Connection Tri-State (High Impedance)

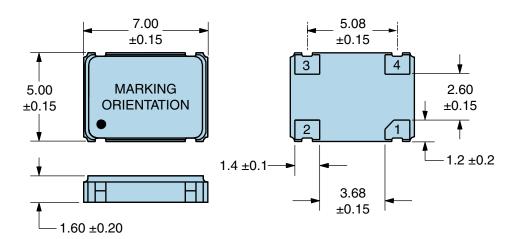
Duty Cycle 50 ±10(%)

Operating 260°C F ping at 25°C ±5ppm/ perating Temperature Range -40°C to pply Voltage 1.8Vdc to put Current 3.5mA N atput Voltage Logic High (Voh) 90% of the put Voltage Logic Low (Vol) 10% of the perating tiput Voltage Logic Low (Vol) 50 ±10(the put Voltage Logic Low (Vol) 50 ±10(the pu	n Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the ng Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, Reflow, Shock, and Vibration) Year Maximum 0 +85°C
Operating 260°C F #5ppm/ perating Temperature Range -40°C to pply Voltage 1.8Vdc at the proof of the proof o	ng Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, Reflow, Shock, and Vibration) Year Maximum > +85°C ±5% Maximum (No Load)
perating Temperature Range -40°C to pply Voltage 1.8Vdc 3.5mA N atput Voltage Logic High (Voh) 10% of se/Fall Time 6nSec N aty Cycle ad Drive Capability -40°C to 1.8Vdc 3.5mA N 90% of 1.8Vdc	±5% Maximum (No Load)
pply Voltage 1.8Vdc: 3.5mA N itput Voltage Logic High (Voh) itput Voltage Logic Low (Vol) 10% of se/Fall Time 6nSec N ity Cycle ad Drive Capability 1.8Vdc: 3.5mA N 90% of 6nSec N 50 ±10(±5% Maximum (No Load)
out Current 3.5mA M 1tput Voltage Logic High (Voh) 10% of	Maximum (No Load)
triput Voltage Logic High (Voh) triput Voltage Logic Low (Vol) se/Fall Time fin Sec N try Cycle ad Drive Capability 90% of 10% of 50 ±10(15pF M	
tering the structure of	Vdd Minimum (IOH = -8mA)
se/Fall Time 6nSec M aty Cycle 50 ±10(ad Drive Capability 15pF M	
ad Drive Capability 50 ±10(15pF Ma	Vdd Maximum (IOL = +8mA)
ad Drive Capability 15pF M	Maximum (Measured at 20% to 80% of waveform)
	%) (Measured at 50% of waveform)
tput Logic Type CMOS	aximum
n 1 Connection Tri-State	e (High Impedance)
-State Input Voltage (Vih and Vil) 90% of Impeda	Vdd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High nce)
andby Current 10µA M	aximum (Pin 1 = Ground)
solute Clock Jitter ±100pS	ec Maximum
art Up Time 10mSec	Maximum
orage Temperature Range -55°C to	

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)

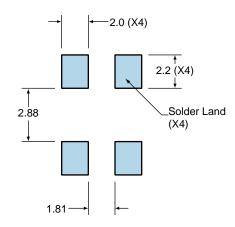


PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	5.000M
3	XXXXXX XXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

All Dimensions in Millimeters



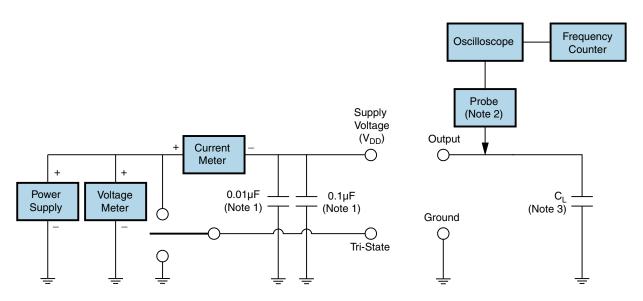
All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value C₁ includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

<u> </u>	
T _s MAX to T _∟ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)